
 $^{51}\text{V}(\alpha, t)$ 1989Pe06, 1968Ma37, 1978Le08

Type	Author	History	Citation	Literature Cutoff Date
Full Evaluation	Yang Dong, Huo Junde		NDS 128, 185 (2015)	10-Jul-2015

Target $J^\pi=7/2^-$.

1968Ma37: E=29 MeV, FWHM \approx 110 keV, $\sigma(E(t), \theta)$, E- ΔE semiconductor detector assembly, 1000 μm thick stopping detector, 3 MM diam ΔE detector, DWBA analysis.

1978Le08: E=25 MeV, $\sigma(E, \theta)$, E- ΔE silicon semiconductor detector telescope, E-detectors were about 1 mm thick, ΔE detectors were from 60 to 140 μm thick, DWBA analysis.

1989Pe06: E=80.9 MeV, $\sigma(E, \theta)$, QDDM spectrometer, DWBA analysis.

Others: 1976ToZK.

Data for E(level)<6000 are from 1968Ma37; others are from 1989Pe06, except as noted.

 ^{52}Cr Levels

E(level)	L	C^2S	Comments
0.0	3	0.50 [‡]	C^2S : 0.57 (1978Le08).
1430	3	0.68 [‡] 10	C^2S : 0.82 (1978Le08).
2370	3	0.53 [‡] 10	
2770	3	0.81 [‡] 10	
3110 40	3	1.72 [‡] 20	
3440 40	3,(1)	0.05 [‡] 5	
3800 40	3,(1)	0.05 [‡] 5	
4.10×10^3 10			
4.68×10^3 10	1		
5.12×10^3 10	1		
5.45×10^3 10	1		
5.83×10^3 10	1		
7.81×10^3	4	0.88 [†]	
8.01×10^3	4	0.46 [†]	
8.19×10^3	4	0.69 [†]	
8.42×10^3	4	0.015	
9.48×10^3	4	0.032	
9.63×10^3	4	0.012	
10.13×10^3	4	0.019	
10.28×10^3	4	0.039	
11.17×10^3	4	0.047	
11.35×10^3	4	0.051	
11.66×10^3	4	0.012	
11.79×10^3	4	0.038	
12.05×10^3	4	0.045	
12.50×10^3	4	0.67 [†]	
12.70×10^3	4	0.011	
13.01×10^3	4	0.36 [†]	
14.47×10^3	4	0.020	
15.28×10^3	4	0.080	T=3
15.482×10^3 7	4	0.121	T=3

[†] $C^2S/(2J_I+1)$ (1989Pe06).

[‡] $(2J_f+1)C^2S/(2J_i+1)$ (1968Ma37).